

10Amp. Schottky Barrier Rectifiers

MBR10200FP

$I_{F(AV)}$	$2 \times 5A$
V_{RRM}	200V
T_j	175°C
$V_F(\text{typ.})$	0.7V

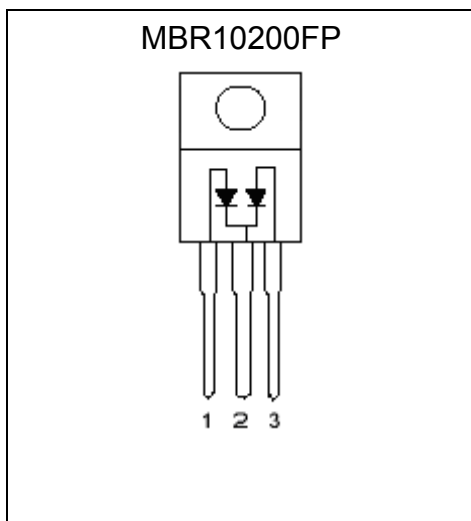
Features

- 175°C operating junction temperature
- Low V_F and low I_R type
- Metal silicon junction, major carrier conduction
- 10A total (5A per diode leg)
- Guardring for over voltage protection
- Low power loss, high efficiency
- High surge capability
- Insulating package, insulating voltage=2500V DC, capacitance=45pF
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection application
- Pb-free lead plating package

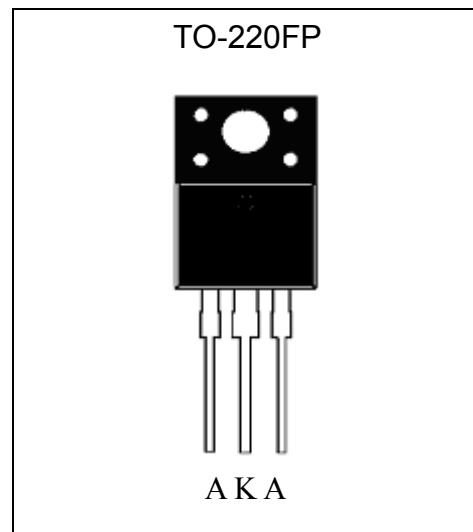
Mechanical Data

- Case: TO-220FP molded plastic
- Mounting Position: Any
- Weight: 2.2 grams, 0.078 ounce approximately
- Terminals: Pure tin plated, lead-free, solderable per MIL-STD-750 method 2026
- Epoxy: UL 94V-0 rate flame retardant
- Mounting torque: 5 in.-lb. maximum

Equivalent Circuit



Outline





Maximum Ratings and Electrical Characteristics (Per Diode Leg)

(Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

Parameter	Symbol	Value	Units
Maximum Recurrent peak reverse voltage	V _{RRM}	200	V
Maximum RMS voltage	V _{RMS}	140	V
Maximum DC blocking voltage	V _{DC}	200	V
Maximum instantaneous forward voltage at (Note 1)	V _F	I _F =5A, T _C =25°C	0.90
		I _F =5A, T _C =125°C	0.74
		I _F =10 A, T _C =25°C	1.00
		I _F =10A, T _C =125°C	0.87
Maximum Average forward rectified current @ T _C =133°C	Per Diode	5	A
	Per Device	10	
Peak repetitive forward current (square wave, 20kHz, T _C =133°C)	I _{FRM}	10	A
Non-repetitive peak forward surge current @ 8.3ms single half sine wave superimposed on rated load (JEDEC method)	I _{FSM}	110	A
Peak repetitive reverse surge current (Note 1), T _J <175°C	I _{RRM}	2	A
Maximum instantaneous reverse current at	I _R	V _R =200 V, T _C =25°C	5 μA
		V _R =200 V, T _C =125°C	5 mA
Voltage rate of change, (rated V _R)	dV/dt	10,000	V/μs
Typical junction capacitance @ f=1MHz and applied 5V reverse voltage	C _J	65 (typ.)	pF
ESD susceptibility (Note 2)		8000	V
Operating junction and storage temperature range	T _J ; T _{stg}	-65 ~ +175	°C

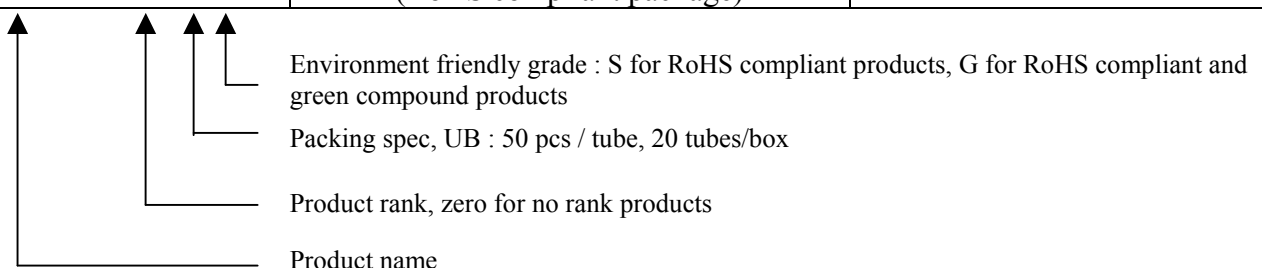
Notes : 1. 2.0μs pulse width, f=1.0kHz
 2. Human body model, 1.5kΩ in series with 100pF

Thermal Data

Parameter	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-case	R _{th,j-c}	3.5	°C/W
Maximum Thermal Resistance, Junction-to-ambient	R _{th,j-a}	60	°C/W
Lead Temperature for Soldering Purposes : 1/8" from Case for 5 seconds	T _L	300	°C

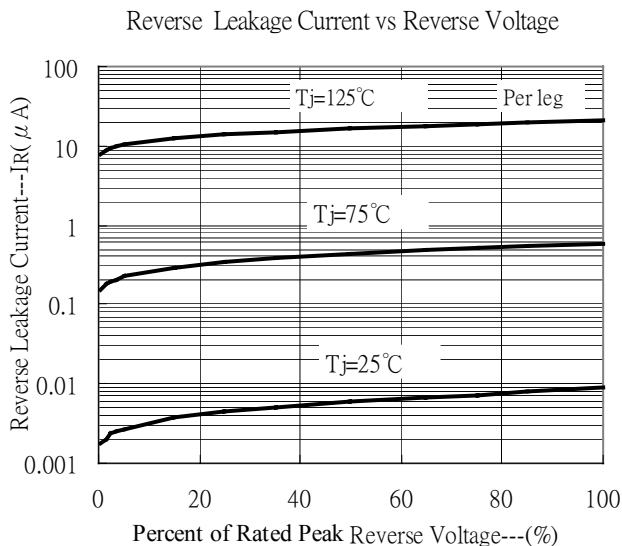
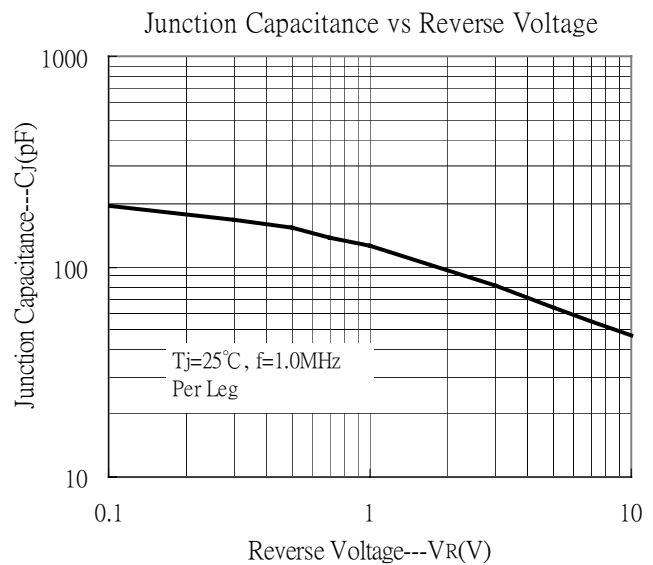
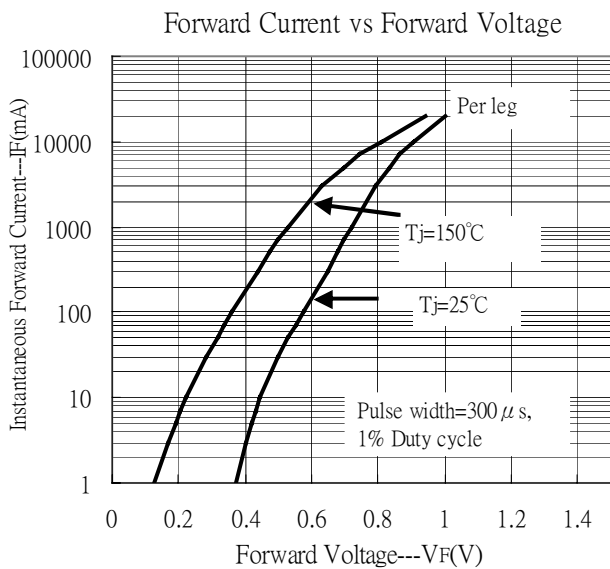
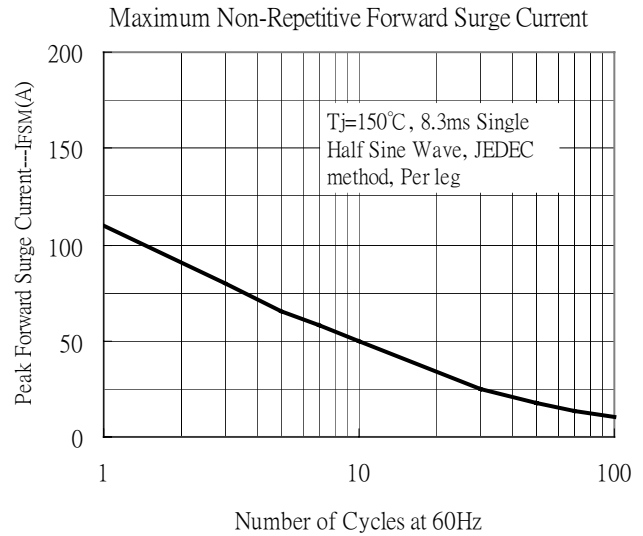
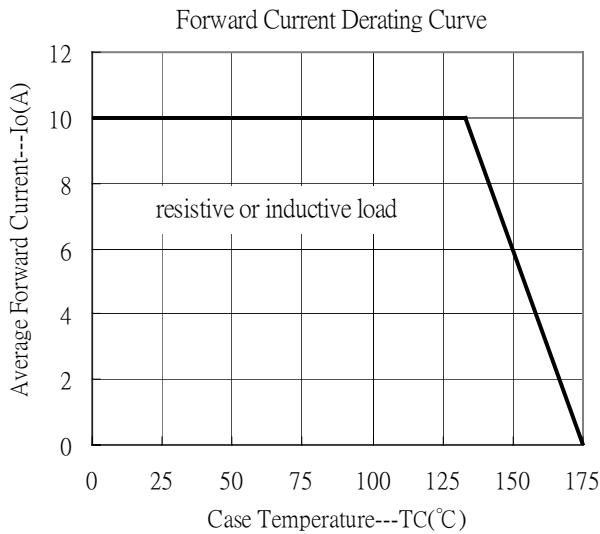
Ordering Information

Device	Package	Shipping
MBR10200FP-0-UB-S	TO-220FP (RoHS compliant package)	50 pcs / Tube, 40 Tubes/Box



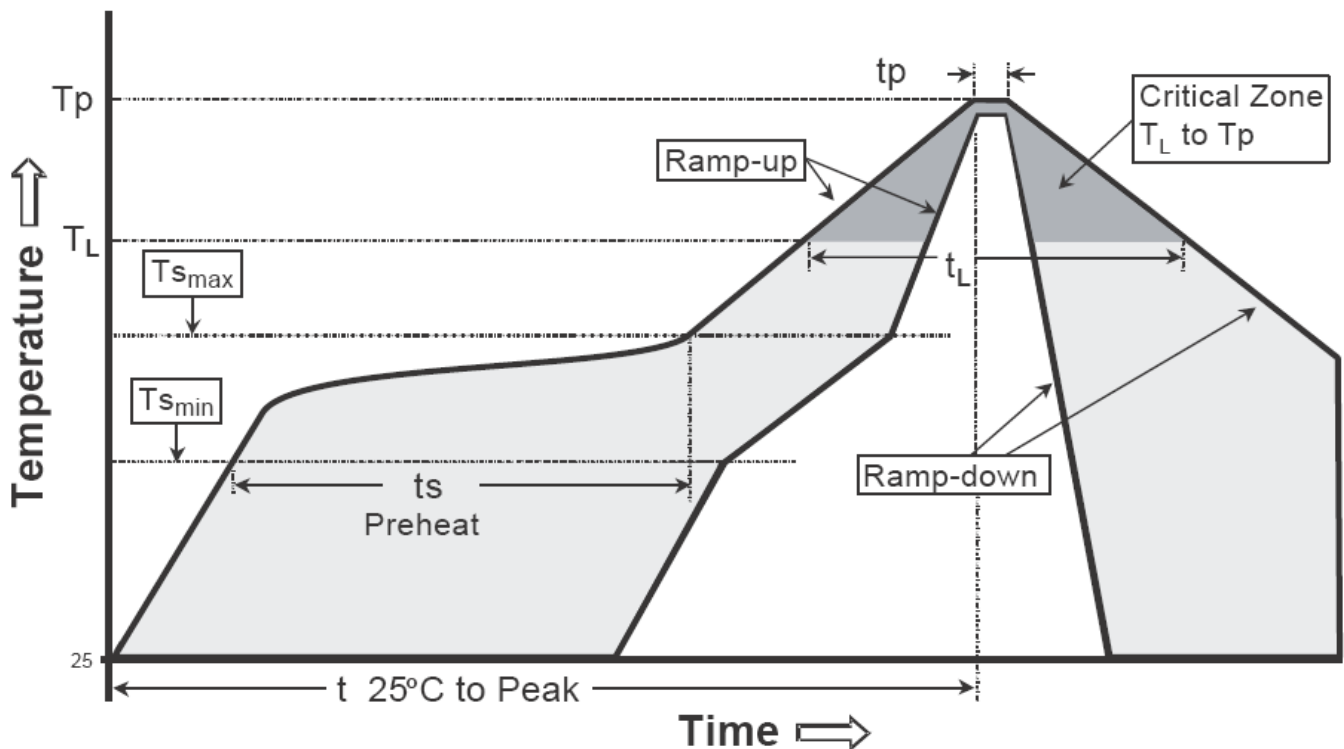


Typical Characteristics



Recommended wave soldering condition

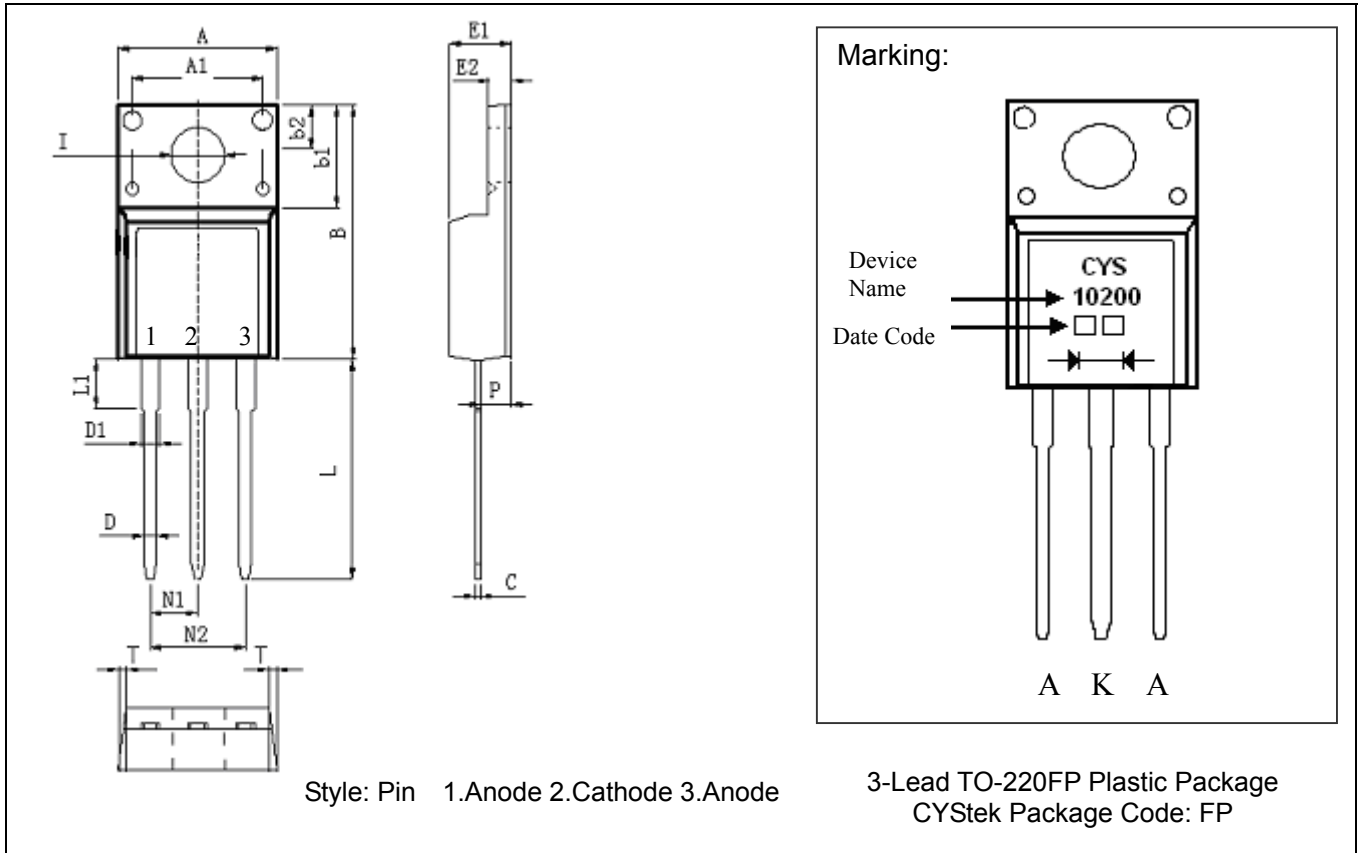
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-220FP Dimension(K Forming)



Style: Pin 1.Anode 2.Cathode 3.Anode

3-Lead TO-220FP Plastic Package
 CYStek Package Code: FP

*: Typical

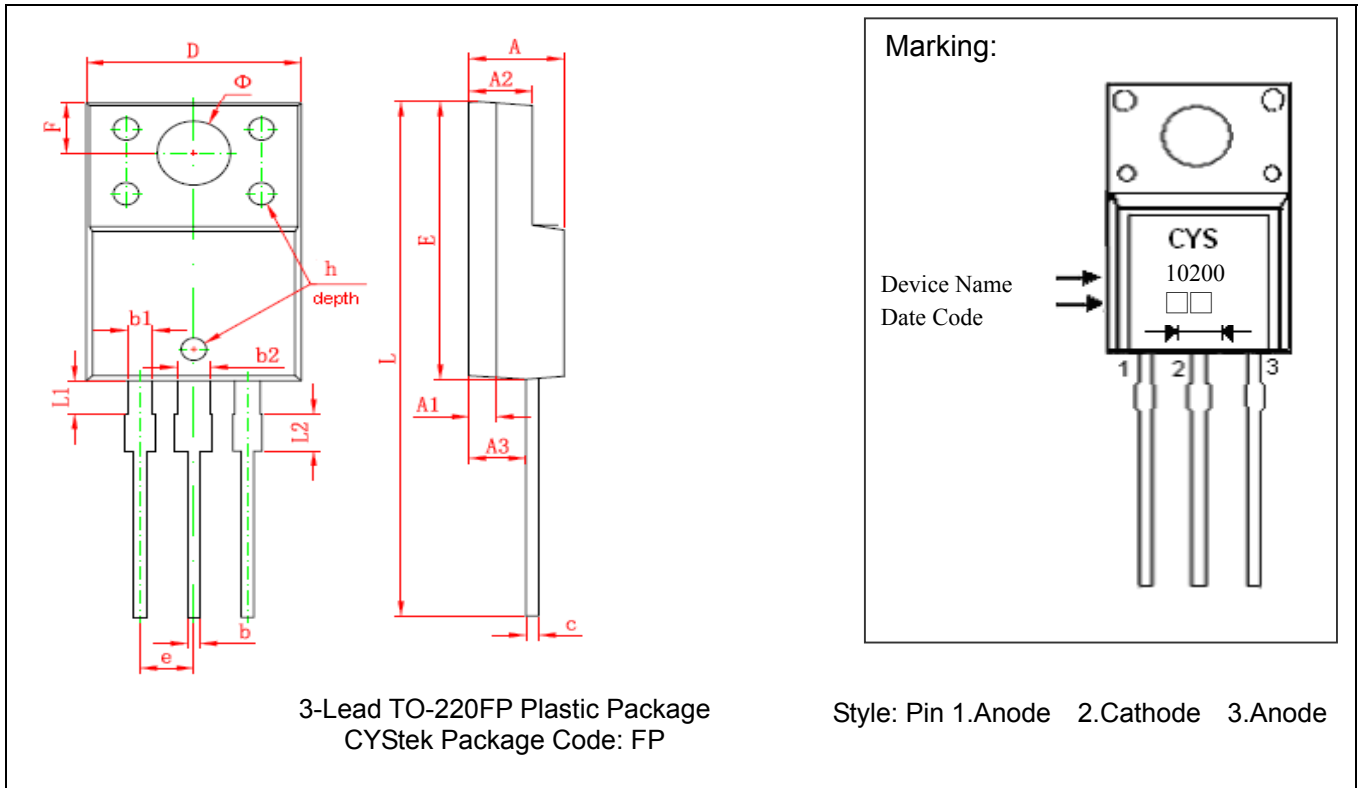
DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.3740	0.4134	9.50	10.50	E2	0.0984	0.1063	2.50	2.70
A1	*0.2756		*7.00		N1	0.0961	0.1039	2.44	2.64
B	0.6063	0.6299	15.40	16.00	N2	0.1921	0.2079	4.88	5.28
b1	0.2480	0.2717	6.30	6.90	P	0.0984	0.1142	2.50	2.90
b2	0.0984	0.1181	2.50	3.00	L	0.5276	0.5354	13.40	13.60
C	0.0138	0.0295	0.35	0.75	L1	0.1378	0.1772	3.50	4.50
D	0.0276	0.0354	0.70	0.90	I	0.1181	0.1339	3.00	3.40
D1	0.0394	0.0551	1.00	1.40	T	0.0059	0.0138	0.15	0.35
E1	0.1693	0.1850	4.30	4.70					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

TO-220FP (C Forming) Dimension



3-Lead TO-220FP Plastic Package
 CYStek Package Code: FP

Style: Pin 1.Anode 2.Cathode 3.Anode

*Typical

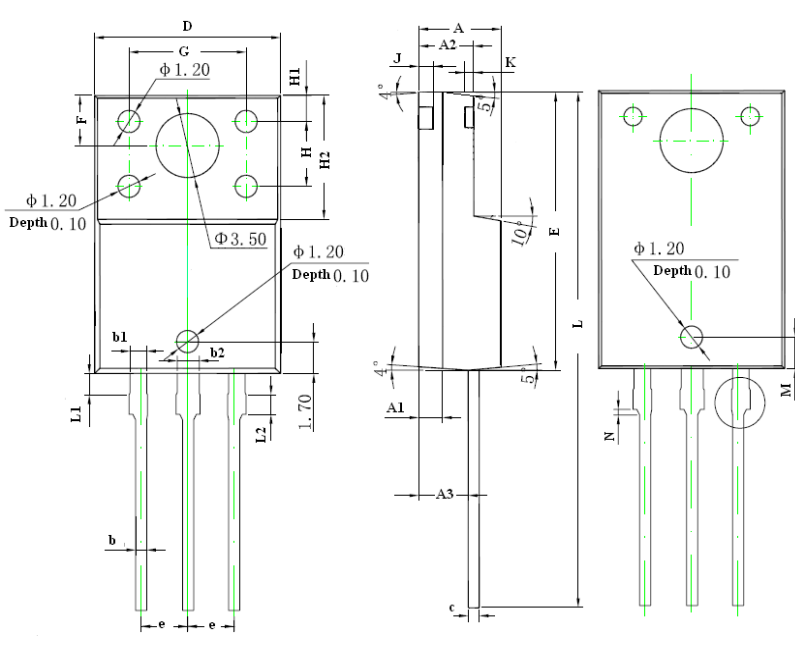
DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.169	0.185	4.300	4.700	E	0.583	0.598	14.800	15.200
A1	0.051 REF		1.300 REF		e	0.100*		2.540*	
A2	0.110	0.126	2.800	3.200	F	0.106	REF	2.700	REF
A3	0.098	0.114	2.500	2.900	Φ	0.138	REF	3.500	REF
b	0.020	0.030	0.500	0.750	h	0.000	0.012	0.000	0.300
b1	0.043	0.053	1.100	1.350	L	1.102	1.118	28.000	28.400
b2	0.059	0.069	1.500	1.750	L1	0.067	0.075	1.700	1.900
c	0.020	0.030	0.500	0.750	L2	0.075	0.083	1.900	2.100
D	0.392	0.408	9.960	10.360					

- Notes: 1.Controlling dimension: millimeters.
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Material:

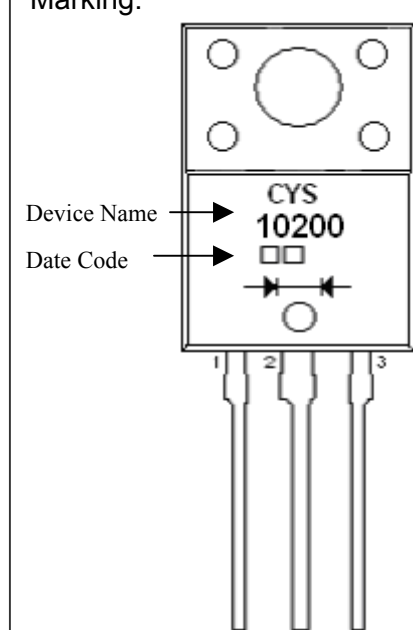
- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

TO-220FP (S Forming) Dimension



3-Lead TO-220FP Plastic Package
 CYStek Package Code: FP

Marking:



Device Name →
 Date Code →

Style: Pin 1.Anode 2.Cathode 3.Anode

*Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.171	0.183	4.35	4.65	G	0.246	0.258	6.25	6.55
A1	0.051 REF		1.300 REF		H	0.138 REF		3.50	REF
A2	0.112	0.124	2.85	3.15	H1	0.055 REF		1.40	REF
A3	0.102	0.110	2.60	2.80	H2	0.256	0.272	6.50	6.90
b	0.020	0.030	0.50	0.75	J	0.031 REF		0.80	REF
b1	0.031	0.041	0.80	1.05	K	0.020		0.50	REF
b2	0.047 REF		1.20 REF		L	1.102	1.118	28.00	28.40
c	0.020	0.030	0.500	0.750	L1	0.043	0.051	1.10	1.30
D	0.396	0.404	10.06	10.26	L2	0.036	0.043	0.92	1.08
E	0.583	0.598	14.80	15.20	M	0.067 REF		1.70	REF
e	0.100 *		2.54*		N	0.012	REF	0.30	REF
F	0.106 REF		2.70 REF						

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Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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